

**In the Claims:**

**Claim 1 (previously presented):** A flash memory device, comprising:

- a. a substrate;
- b. at least one core stack, wherein the at least one core stack comprises:
  - (1) a tunnel oxide layer on the substrate;
  - (2) a first polysilicon layer on the tunnel oxide layer;
  - (3) an anti-reflective interpoly layer atop and in contact with the first polysilicon layer; and
  - (4) a transmissive second polysilicon layer on the anti-reflective interpoly layer;
- c. at least one source region adjacent to the at least one core stack; and
- d. at least one drain region adjacent to the at least one core stack.

**Claim 2 (previously presented):** The flash memory device, as recited in Claim 1, wherein the at least one source region and the at least one drain region are formed by the method comprising the steps of:

- a. depositing a layer of photoresist over the substrate and the at least one core stack;
- b. illuminating the layer of photoresist with a light;
- c. transmitting some of the light through the transmissive second polysilicon layer;

- d. preventing the reflection of the light at the anti-reflective interpoly layer;
- e. removing part of the photoresist layer; and
- f. implanting a dopant into the substrate.

**Claim 3 (original):** The flash memory device, as recited in Claim 2, wherein the light has a wavelength  $\lambda_1$ , and wherein the anti-reflective interpoly layer has an index of refraction  $n$  and a thickness  $d$ , and wherein the light has an integer number  $m$  wavelengths incident upon the anti-reflective interpoly layer, and wherein

$$d \cong \frac{(m + \frac{1}{2})\lambda_1}{2n}, \text{ where } m = 0, 1, 2, \dots$$

**Claim 4 (original):** The flash memory device, as recited in Claim 2, wherein the light has a wavelength  $\lambda_1$ , and wherein the anti-reflective interpoly layer has an index of refraction  $n$ , and a thickness  $d$ , wherein

$$d \cong \frac{\lambda_1}{4n}.$$

**Claim 5 (original):** The flash memory device, as recited in Claim 4, wherein the anti-reflective interpoly layer is made of silicon oxynitride (SiON).

**Claim 6 (original):** The flash memory device, as recited in Claim 5, wherein the thickness of the anti-reflective interpoly layer is between about 300 to 400 Å thick.

Attorney Docket No.: 0180221

**Claim 7 (original):** The flash memory device, as recited in Claim 2, wherein the step of depositing the layer of photoresist, deposits the photoresist onto a surface of the transmissive second polysilicon layer.

**Claim 8 (original):** The flash memory device, as recited in Claim 1, wherein the anti-reflective interpoly layer is made of silicon oxynitride.

**Claim 9 (original):** The flash memory device, as recited in Claim 8, wherein the thickness of the anti-reflective interpoly layer is between about 300 to 400 Å thick.

**Claims 10-15 (canceled)**